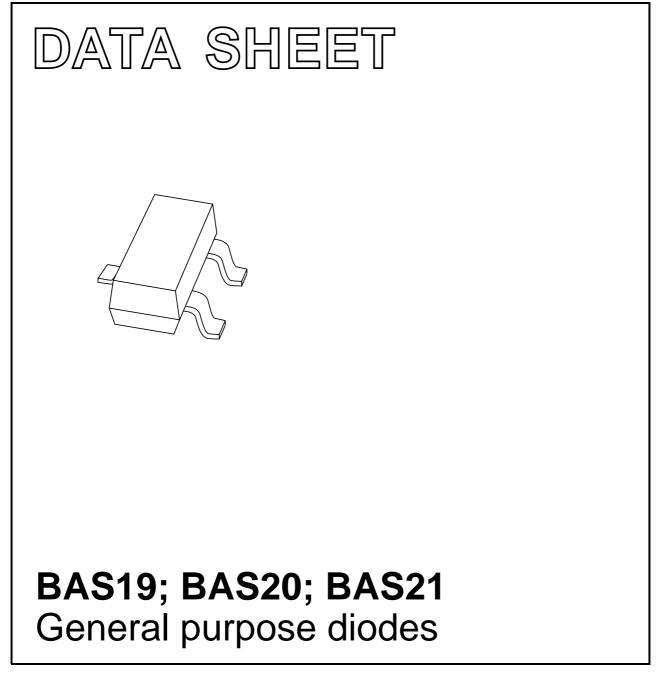
DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 1999 May 26 2003 Mar 20



FEATURES

- Small plastic SMD package
- Switching speed: max. 50 ns
- General application
- Continuous reverse voltage: max. 100 V; 150 V; 200 V
- Repetitive peak reverse voltage: max. 120 V; 200 V; 250 V
- Repetitive peak forward current: max. 625 mA.

APPLICATIONS

• General purpose switching in e.g. surface mounted circuits.

DESCRIPTION

The BAS19, BAS20 and BAS21 are general purpose diodes fabricated in planar technology, and encapsulated in a small SOT23 plastic SMD package.

MARKING

TYPE NUMBER	MARKING CODE (1)
BAS19	JP*
BAS20	JR*
BAS21	JS*

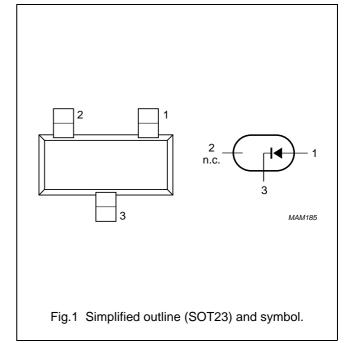
Note

- 1. * = p: Made in Hong Kong.
 - * = t: Made in Malaysia.
 - * = W: Made in China.

PINNING

PIN	DESCRIPTION	
1	anode	
2	not connected	
3	cathode	

BAS19; BAS20; BAS21



BAS19; BAS20; BAS21

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{RRM}	repetitive peak reverse voltage				
	BAS19		_	120	V
	BAS20		_	200	V
	BAS21		_	250	V
V _R	continuous reverse voltage				
	BAS19		_	100	V
	BAS20		-	150	V
	BAS21		-	200	V
I _F	continuous forward current	see Fig.2; note 1	-	200	mA
I _{FRM}	repetitive peak forward current		-	625	mA
I _{FSM}	non-repetitive peak forward current	square wave; T _j = 25 °C prior to surge; see Fig.4			
		t = 1 μs	_	9	А
		t = 100 μs	_	3	А
		t = 10 ms	-	1.7	А
P _{tot}	total power dissipation	T _{amb} = 25 °C; note 1	-	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C

Note

1. Device mounted on an FR4 printed-circuit board.

BAS19; BAS20; BAS21

ELECTRICAL CHARACTERISTICS

 $T_j = 25 \ ^{\circ}C$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
V _F	forward voltage	see Fig.3		
		I _F = 100 mA	1	V
		I _F = 200 mA	1.25	V
I _R	reverse current	see Fig.5		
	BAS19	V _R = 100 V	100	nA
		V _R = 100 V; T _j = 150 °C	100	μA
	BAS20	V _R = 150 V	100	nA
		V _R = 150 V; T _j = 150 °C	100	μA
	BAS21	V _R = 200 V	100	nA
		V _R = 200 V; T _j = 150 °C	100	μA
C _d	diode capacitance	$f = 1 \text{ MHz}; V_R = 0; \text{ see Fig.6}$	5	pF
t _{rr}	reverse recovery time	when switched from $I_F = 30$ mA to $I_R = 30$ mA; $R_L = 100 \Omega$; measured at $I_R = 3$ mA; see Fig.8	50	ns

THERMAL CHARACTERISTICS

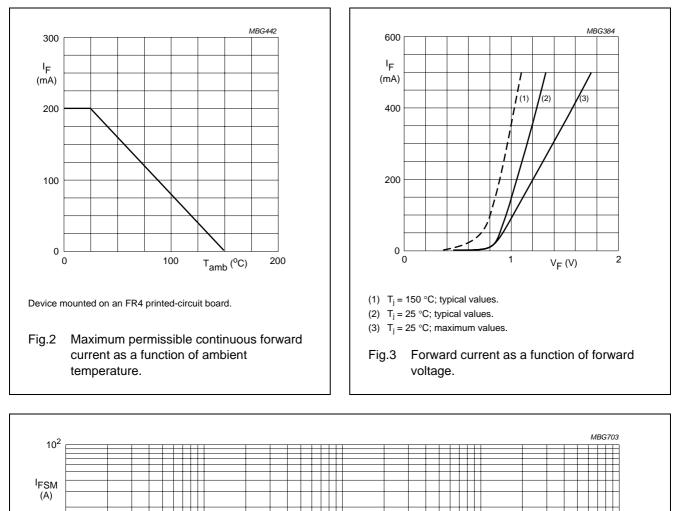
SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-tp}	thermal resistance from junction to tie-point		330	K/W
R _{th j-a}	thermal resistance from junction to ambient	note 1	500	K/W

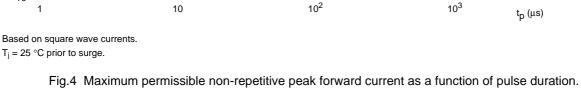
Note

1. Device mounted on an FR4 printed-circuit board.

BAS19; BAS20; BAS21

GRAPHICAL DATA





10

1

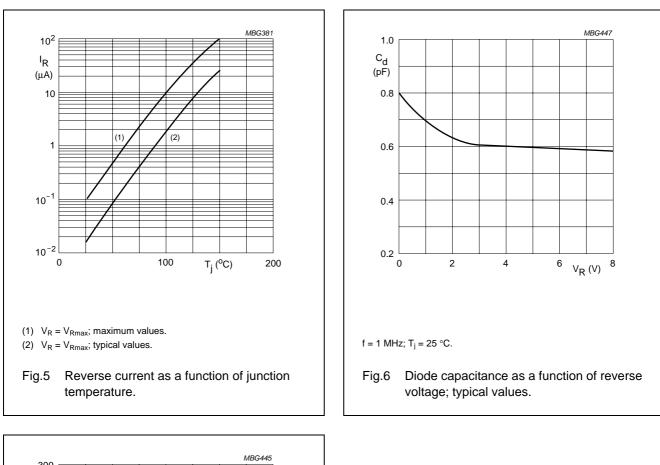
10⁻¹

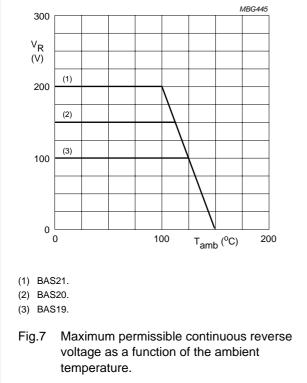
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10⁴

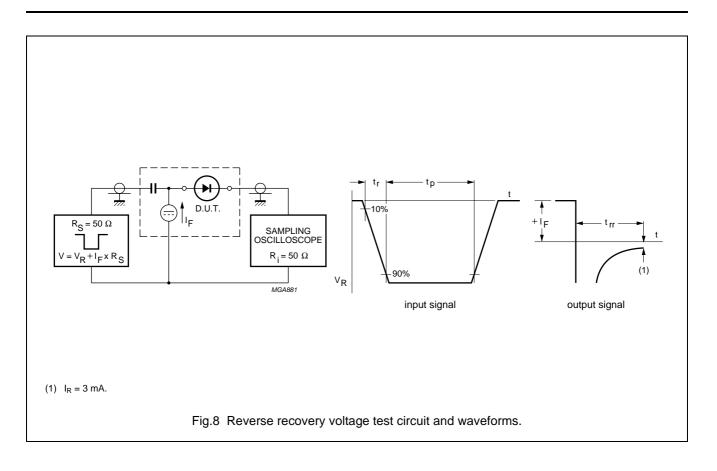
t_p (μs)

BAS19; BAS20; BAS21





BAS19; BAS20; BAS21

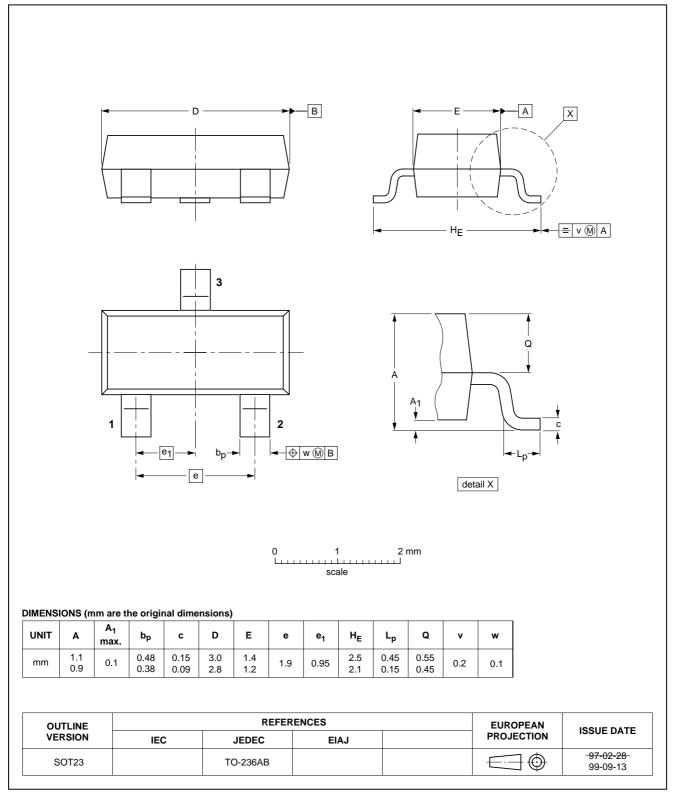


BAS19; BAS20; BAS21

General purpose diodes

PACKAGE OUTLINE





BAS19; BAS20; BAS21

DATA SHEET S	STATUS
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DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
- The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors. No changes were made to the content, except for the legal definitions and disclaimers.

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Printed in The Netherlands

613514/04/pp10

Date of release: 2003 Mar 20

Document order number: 9397 750 10961

